In re Appln. of Naruhiko KAJI Application No. Unassigned

## SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 6 with:

The present invention relates to a wiring structure in a semiconductor device, and particularly to a multi-layer wiring structure using a porous low-k dielectric film as <u>an</u> interlayer dielectric film, and <u>a</u> copper wiring.